

# Development of Anodised Aluminium Oxide Nanostructure from Al-Mn Alloy

VOON CHUN HONG 0940410410

A thesis submitted in fulfillment of the requirements for the degree of Doctor of Philosophy

School of Materials Engineering UNIVERSITI MALAYSIA PERLIS

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		DECLARATION OF THESIS
Author's full name	:	VOON CHUN HONG
Date of birth	:	5 <sup>th</sup> MARCH 1985
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	used for the fabrication of Al-Mn alloys of different compositions	

## LIST OF ABBREVIATIONS, SYMBOLS OR NOMENCLATURES

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AAO Anodic aluminium oxide

AFM Atomic force microscope

Al-Mn Aluminium manganese

Al<sup>3+</sup> Aluminium ions

Al<sub>2</sub>O<sub>3</sub> Aluminium oxide

Au Gold

BMP Bitmap

CdS Cadmium sulfide

CNT Carbon nanotube

Cu Copper

DC Direct Current

DUV Deep ultraviolet

EDX Element dispersive X ray spectroscopy

FFT Fast Fourier transform

Fe Iron

GPa Giga pascal

H<sup>+</sup> Hydrogen ions

Mg Magnesium

Mn Manganese

O<sup>2</sup>- Oxygen ions

OH Hydroxide ions

PBR Pilling Bedworth ratio

Pd Palladium

Pt Platinum

PTFE Polytetrafluoroethylene

SEM Scanning electron microscope

Si Silicon

SPM Scanning probe microscope

TSA Templated self assembly

XRD X-ray diffraction

ZnO Zinc oxide

 $A_t$  Area of sample

at% Atomic percent

F Faraday constant

g/cm<sup>3</sup> Gram per cubic centimetre

g/mol Gram per mole

j Current density

mA/cm<sup>2</sup> Milliampere per square centimetre

 $M_{Al_2O_3}$  Molecular weight of aluminium oxide

 $m_{Al}$  Mass of aluminium metal converted to oxide

Molecular weight of aluminium metal

Mass of aluminium metal calculated using equation

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 $(m_{Al})_{\eta=100}$  with  $\eta=100\%$ 

 $m_{di}$  Mass of specimen before dissolution

 $m_{df}$ . Mass of specimen after the dissolution

 $m_i$  Mass of sample before anodising

 $m_f$  Mass of sample after anodising

 $m_p$  Total mass of porous oxide

Time t

Weight percent wt %

Number of electrons changed in reaction Z.

% Percent

 $^{\mathrm{o}}\mathrm{C}$ Degree Celsius

O This item is protected by original copyright  $\Delta G^{o}/n$ Gibbs free energy per equivalent

#### Perkembangan Aluminium Oksida Teranod Daripada Aloi Al-Mn

#### **ABSTRAK**

Kajian ini dibahagi kepada dua bahagian. Bahagian pertama kajian ini memberi tumpuan kepada sintesis aluminium oksida teranod (AAO) berliang tersusun dengan menggunakan rawatan pelarutan oksida. AAO berliang telah dihasil dengan penganodan aluminium 99.99% di dalam asid oxalik 0.3 M pada suhu 15°C selama 15 minit. Substrat teranod terdedah kepada rawatan pelarutan oksida dengan direndam di dalam campuran asid kromik dan asid fosforik yang dikacau. Kesan rawatan pelarutan oksida terhadap morfologi dan keteraturan AAO berliang telah dikaji dengan menggunakan mikroskop imbasan elektron. Keputusan menunjukkan pendedahan AAO berliang kepada rawatan pelarutan oksida selama tiga minit mendedahkan susunan liang yang tersusun atur yang terhasil pada peringkat pertumbuhan mantap. Keteraturan AAO berliang telah ditambahbaikkan. Dalam bahagian kedua kajian, AAO berliang telah dihasil daripada substrat aloi aluminium mangan dan kesan kandungan mangan, voltan penganodan, kepekatan asid oxalik dan suhu asid oxalik terhadap sifat penganodan, morfologi, sifat-sifat dimensi dan kinetik pertumbuhan telah dikaji. Keputusan menunjukkan penambahan mangan dari 0.5 wt % hingga 2.0 wt % ke dalam substrat Al mengurangkan ketumpatan arus, keteraturan dan kinetik pertumbuhan AAO berliang. Saiz liang dan jarak antara liang juga didapati berkurang dengan penambahan mangan. Kecekapan arus proses penganodan berkurang apabila kandungan Mn bertambah kepada 1.0 wt %, tetapi meningkat apabila kandungan Mn bertambah kepda 2.0 wt %. Analisa corak XRD menunjukkan alumina amorfus telah terhasil di dalam substrat untuk semua komposisi dan MnO<sub>2</sub> telah didapati di dalam substrat teranod Al-1.5 wt % Mn dan Al -2.0 wt % Mn. Untuk kajian mengenai kesan voltan penganodan, penganodan substrat Al-0.5 wt % di bawah pengaruh voltan penganodan yang meningkat dari 30 - 70V telah membawa kepada ketumpatan arus yang lebih tinggi, Saiz liang, jarak antara liang yang lebih besar dan kadar pertumbuhan yang lebih tinggi. Keteraturan susunan liang AAO berliang telah dipertingkatkan apabila voltan penganodan dinaikkan dari 30 V kepada 50 V, tetapi merosot apabila dipertingkatkan kepada 70 V. Pecahan dielektrik berlaku apabila penganodan dijalankan pada 70 V. Didapati amaun alumina amorfus bertambah apabila voltan penganodan dinaikkan dari 30 V kepada 70 V. Penganodan Al-0.5 wt % Mn pada 50 V dalam asid oxalik yang kepekatannya meningkat dari 0.1 M kepada 0.7 M menigkatkan ketumpatan arus dan kinetik pertumbuhan. AAO berliang tersusun diperolehi apabila asid oksalik yang kepekatannya kecuali 0.1 M digunakan. Pertambahan kepekatan asid oxalik mengurangkan saiz liang manakala tiada perbezaan ketara antara jarak antara liang diperhati. Kecekapan arus berkurang dengan fungsi kepekatan asid oxalik. Keamatan relatif puncak luas dalam corak XRD menunjukkan amaun alumina amorfus meningkat dengan fungsi kepekatan asid oxalik. Untuk kajian kesan suhu asid oxalik, penganodan Al-0.5 wt % Mn pada 50 V dibuat dalam asid oxalik 0.5 M antara suhu 5 °C hingga 25 °C. Ketumpatan arus dan kinetik pertumbuhan bertambah manakala keteraturan susunan liang dan kecekapan arus berkurang dengan suhu asid oxalik yang meningkat. Suhu asid oxalik tidak mempunyai kesan ketara terhadap kedua-dua saiz liang dan jarak antara liang. Keamatan relatif puncak luas meningkat menunjukkan amaun alumina amorfus bertambah dengan peningkatan suhu asid oxalik.

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#### Development of Anodised Aluminium Oxide Nanostructure from Al-Mn Alloy

#### **ABSTRACT**

This study was divided into two parts. The first part of the study was focused on the synthesis of well ordered porous AAO by using oxide dissolution treatment. The porous AAO was formed by anodising of 99.99 % aluminium in 0.3 M oxalic acid at 15 °C for 15 minutes. Anodised substrates were subjected to oxide dissolution treatment by immersing in stirred mixture of chromic acid and phosphoric acid. The effect of oxide dissolution treatment on the morphology and regularity of porous AAO was studied by using scanning electron microscope. The results showed that exposure of porous AAO to oxide dissolution treatment up to three minutes revealed the well ordered pores arrangement that formed during the steady state growth stage. Regularity of the porous AAO was improved. In the second part of the study, porous AAO was formed from aluminium manganese (Al-Mn) alloy substrates and the effect of manganese content, anodising voltage, concentration of oxalic acid, and temperature of oxalic acid on the anodising behaviour, morphology, dimensional properties and growth kinetics were studied. Results showed that the addition of Mn from 0.5 wt % to 2.0 wt % into Al substrates reduced the current density, regularity and growth kinetics of porous AAO. The pore size and interpore distance were also found to decrease with the addition of Mn. Anodising efficiency of anodising process decreased as the Mn content increased up to 1.0 wt %, but increased when the Mn content was further increased to 2.0 wt %. Analysis of XRD patterns showed that amorphous alumina was formed in substrates of all compositions and MnO<sub>2</sub> was found to present in Al-1.5 wt % Mn and Al -2.0 wt % Mn substrates. For the study of effect of anodising voltage, anodising of Al-0.5 wt % Mn under the influence of increasing anodising voltage of 30-70V has led to higher current density, larger pore size and interpore distance and higher growth rates. The regularity of pore arrangement of porous AAO was improved when the anodising voltage was increased from 30 V to 50V, but deteriorated when further increased to 70V. Dielectric breakdown occurred when anodising was conducted at 70V. Amount of amorphous alumina was found to increase when the anodising voltage was increased from 30 V to 70 V. Anodising of Al-0.5 wt % Mn at 50 V in oxalic acid of increasing concentration from 0.1 M to 0.7 M increased the current density and growth kinetics. Well ordered porous AAOs were obtained when oxalic acid of all concentration was used, except 0.1 M. Increase of concentration of oxalic acid decreased the pore size while no significant difference in interpore distance was observed. Anodising efficiency decreased as a function of concentration of oxalic acid. The relative intensity of broad peaks in XRD patterns showed that amount of amorphous alumina increased as a function of concentration of oxalic acid. For the study of effect of temperature of oxalic acid, anodising of Al-0.5 wt % Mn was conducted at 50V in 0.5 M oxalic acid of temperature ranging from 5°C to 25°C. Current density and oxide thickness increased while regularity of pores arrangement and anodising efficiency decreased with the increasing temperature of oxalic acid. Temperature of oxalic acid did not have obvious effect on both pore size and interpore distance. Relative intensities of broad peaks increased indicating the amount of amorphous alumina increased with the increasing temperature of oxalic acid.

#### **CHAPTER 1**

#### INTRODUCTION

#### 1.1 Introduction

Nanotechnology primarily involves the study of control and manipulation of matter at nanometre scale. These matters, known as nanostructured material, are defined as materials whose basic units with at least one dimension falls within the range of one to one hundred nanometres (Gogotsi, 2006). The confined dimensionality of these nanostructured materials has led to the discovery of novel biological, chemical and physical properties of these materials. Novel and unique properties of nanostructured materials are attributed to the specific size effect and quantum confinement effect. Controlled manipulation of these properties has led to new devices and technologies. For example, due to the size and shape dependant properties, gold nanoparticle is red in colour instead of golden colour for bulk material (Bhattacharya & Srivastava, 2003). The change in colour of the gold nanoparticles indicates the change in the optical properties and they have bio applications in four area, which are labelling, delivery, heating and sensing (Sperling et al., 2008). Due to the good lubricative property and softness of graphite, it is used in the making of pencils. The structure of carbon nanotube (CNT) is considered similar to that of graphite in which the CNT is conceptualized as a single or multiple rolled layers of graphite. However, the mechanical strength of CNT which has similar structure to that of graphite is higher than the mechanical strength of stainless steel (Yu et al., 2000). This high strength leads to extensive applications of CNT as reinforcement in various matrixes (Cha et al., 2005; Echeberria et al., 2011; Gojny et al., 2004). The confined dimensionality in the nanometre scale has lead to the discovery of novel properties of nanostructured materials. Thus, there is an increasing research interest on the synthesis, characterisation, exploration and exploitation of nanostructured materials.

Generally, there are two approaches to control and manipulate the size of nanostructured materials, which are top-down approach and bottom-up approach. Top-down approach is the successive manipulation of bulk material to obtain nanostructured material. The most commonly used top-down approach is the lithographic method. Lithographic method involves the adding and patterning of layers of materials on the wafer surface. Nanostructures are then formed by selectively etching away materials of certain area. Today, lithography method has revolutionized human lives in the way we communicate, travel, and interact. Although top-down approach provides a promising way to produce nanostructured materials, the use of lithography methods in the fabricating of nanostructured materials faces limitation in the achievable smallest length scale and highest aspect ratio of the nanostructured materials.

Bottom-up approach also played an important role in the development of nanotechnology. The principle behind the bottom-up approach is the self assembly process. Self assembly process provides a route to spontaneous generation and hierarchical organisation of materials by biological or chemical process for the fabrication of nanostructured materials (Lin et al., 2001; Zhang et al., 2002). Bottom-up approach is increasingly being used as an alternative for the fabrication of nanostructured materials due to the fact that it allows smaller geometries than the lithography methods. Furthermore, it is more economic than lithography methods because it does not waste material to etch and does not employ high cost electron beam

lithography techniques. Examples of nanostructured materials fabricated by self assembly methods are arrays of magnetic nanowires which maybe useful as data storage media (Nielsch et al., 2001) and type 1 collagen which maybe useful in tissue engineering and synthesis of biosensor (Xu et al., 2009). However, the weakness of self assembly process in the synthesis of nanostructured materials is the low degree of control over the regularity and uniformity of the nanostructured materials. This is due to the fact that structure of self assembled nanostructured materials is formed based on their own guiding or driving force. This limits the structure and design of self assembled nanostructured materials.

With a template, more complicated designs can be achieved by self assembly method. Therefore, templated self assembly (TSA) was used for the fabrication of nanostructured materials. TSA combines both the top-down and bottom-up approaches to fabricate and control the morphology and size distribution of the nanostructured materials by limiting the self forming and self ordering processes to occur in the templates. Examples of TSA include chemically directed (Stoykovich et al., 2007), lithographically assisted (Cheng et al., 2002) and mechanically assisted (Angelescu et al., 2004). Thus, TSA provides the benefits of both lithography and self assembly and has profound potential in the synthesis of nanostructured materials. The major limitation of TSA is the availability of suitable template for the synthesis of nanostructured materials. The discovery of well ordered nanoporous anodic aluminium oxide (AAO) has enlightened their applications as template for TSA.

Initially, anodic alumina was used as corrosion resistance protective coating in 1923 (Durney, 1984). Since then, the range of applications has increased significantly and anodising process was extensively studied and investigated. Generally, there are two types of anodic alumina, namely barrier type and porous type anodic alumina.